

**1. Scope :**

This specification applies to PN silicon photodiode chips,  
Device No. PD-10043-B

**2. Structure :**

- 2-1. Planar type : PN diode.
- 2-2. Electrodes :  
 Top side ( Anode ) : Aluminum alloy .  
 Back side ( Cathode ) : Gold.

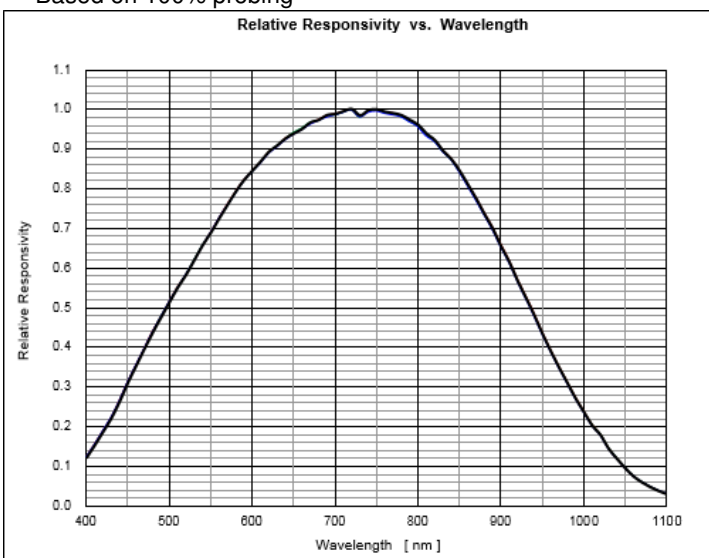
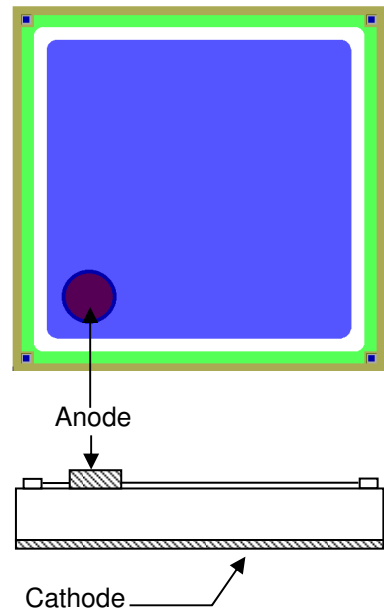
**3. Size :**

- 3-1. Chip size : 43 mils × 43 mils (1.095 mm × 1.095 mm ).
- 3-2. Chip thickness : 8.66 ± 1.0mils (0.220 ± 0.025mm).
- 3-3. Active area : 35.24 mils × 35.24 mils ( 0.895 mm × 0.895 mm ).
- 3-4. Bonding pad ( Anode ) : 6.30 mils (0.160 mm) diameter.
- 3-5. Pattern drawing : Refer to the attached drawing.

**4. Electrical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse dark Current	$I_D$	$V_R=10V$ $E_e=0mW/cm^2$			30	nA
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	30			V
Total Capacitance	$C_t$	$V_R=5V$ $E_e=0mW/cm^2$ $f=1MHz$		TBD		pF

\*Based on 100% probing



\*bare chip measured with integrating sphere